

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings, of claims in the present application:

**Listing of Claims:**

Claims 1-11 (cancelled)

Claim 12 (original) An electric device comprising: a first elongated nanowire on an insulating surface and a second elongated nanowire on said insulating surface at right angles to said first elongated nanowire and separated therefrom by a gap of between 0.4 nm and 10 nm.

Claim 13 (original) The electric device of Claim 12 wherein said first and second nanowires form a transistor having a source, drain, and gate, and wherein said first nanowire has first and second ends;  
said first end of said first nanowire forming said source, said second end of said first nanowire forming said drain, and said second nanowire forming said gate.

Claim 14 (original) The electrical device of Claim 12 wherein said first elongated nanowire comprises a semiconductor chosen from the group consisting of Si, Ge,  $\text{Ge}_x\text{Si}_{1-x}$  where  $0 < x < 1$ , GaAs, InAs, AlGaAs, InGaAs, AlGaAs, GaN, InN, AlN, AlGaIn, and InGaIn.

Claim 15 (original) The electrical device of Claim 12 wherein said gap is filled with a material that stores electrical charge .

Claim 16 (original) The electrical device of Claim 12 wherein said gap is filled with a material having electric dipole moment.

Claim 17 (original) The electrical device of Claim 12 wherein said first and second nanowires form a two-electrode memory switching device, said first nanowire forming the first electrode of said switching device and said second nanowire forming the second electrode of said switching device.